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4V Drive Nch+Nch MOSFET **SP8K31**

●Structure

Silicon N-channel **MOSFET**

Features

- 1) Built-in G-S Protection Diode.
- 2) Small surface Mount Package (SOP8).

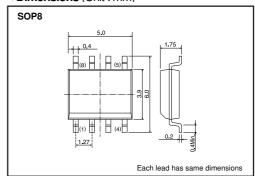
Applications

Switching

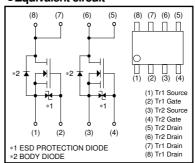
Packaging dimensions

	Package	Taping
Type	Code	TB
	Basic ordering unit (pieces)	2500
SP8K31		0

●Dimensions (Unit:mm)



●Equivalent circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

Parameter		Symbol	Limits	Unit		
Drain-source voltage		V _{DSS}	60	V		
Gate-source voltage		Vgss	±20	V		
Drain current	Continuous	ID	±3.5	Α		
	Pulsed	I _{DP} *1	±14	Α		
Source current (Body diode)	Continuous	Is	1.0	Α		
	Pulsed	Isp *1	14	Α		
Total power dissipation		P _D *2	2.0	W		
Channel temperature		Tch	150	°C		
Range of storage temperature		Tstg	-55 to +150	°C		

^{*1} Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board.

●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	±10	μА	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	60	-	_	٧	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	-	1	μА	VDS= 60V, VGS=0V
Gate threshold voltage	V _{GS (th)}	1.0	_	2.5	٧	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	R _{DS (on)} *	_	85	120	mΩ	I _D = 3.5A, V _{GS} = 10V
		-	100	140	mΩ	I _D = 3.5A, V _{GS} = 4.5V
		_	105	150	mΩ	ID= 3.5A, VGS= 4.0V
Forward transfer admittance	Y _{fs} *	2.5	_	_	S	V _{DS} = 10V, I _D = 3.5A
Input capacitance	Ciss	_	250	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	60	_	рF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	30	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	7	_	ns	V _{DD} ≒ 30V
Rise time	tr *	_	14	_	ns	I _D = 1.8A V _G S= 10V
Turn-off delay time	t _{d (off)} *	_	25	_	ns	$R_{i} = 17\Omega$
Fall time	t _f *	_	7	_	ns	R _G =10Ω
Total gate charge	Qg *	_	3.7	5.2	nC	V _{DD} ≒30V, V _{GS} =5V
Gate-source charge	Q _{gs} *	_	1.2	_	nC	I _D = 3.5A
Gate-drain charge	Q _{gd} *	_	1.2	_	nC	$R_L=8.6\Omega$, $R_G=10\Omega$

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	_	_	1.2	V	I _S =3.5A, V _{GS} =0V

^{*}Pulsed

Electrical characteristic curves

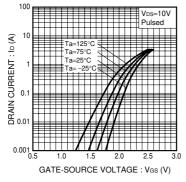


Fig.1 Typical Transfer Characteristics

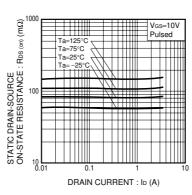


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current(I)

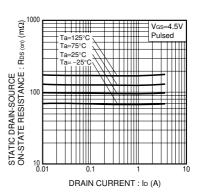


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current(II)

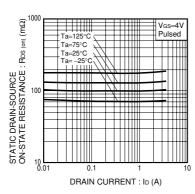


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(III)

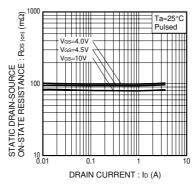


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(IV)

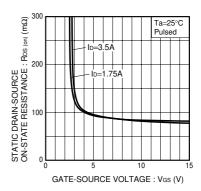


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

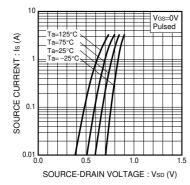


Fig.7 Source Current vs. Source-Drain Voltage

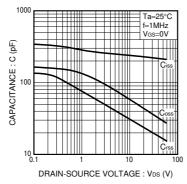


Fig.8 Typical Capacitance vs. Drain-Source Voltage

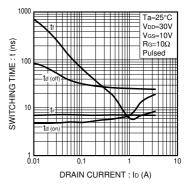


Fig.9 Switching Characteristics

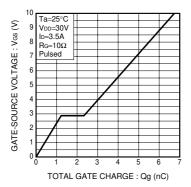


Fig.10 Dynamic Input Characteristics

Measurement circuits

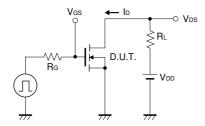


Fig.11 Switching Time Test Circuit

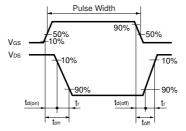


Fig.12 Switching Time Waveforms

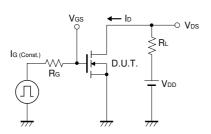


Fig.13 Gate Charge Test Circuit

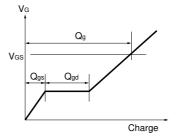


Fig.14 Gate Charge Waveform

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